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Attorney Docket # 203

#8
Amend B
OSMAIS-LOGAN
9402

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Application of)
NAKAJIMA et al.)
Serial No.: 09/635,945 ✓)
Filed: August 10, 2000)
For: Semiconductor Device And Method)
Of Manufacturing The)
Semiconductor Device)
Art Unit: 2811)
Examiner: S. Hu)

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to:	
Commissioner for Patents Washington, D.C. 20231	
on	August 8, 2002
Rachelle Hammerquist	
	8/8/02
Signature	Date

Commissioner for Patents
Washington, D.C. 20231

AMENDMENT B

In response to the Office Action of April 8, 2002, a one month extension of time being separately requested, please amend the above-identified application as follows:

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IN THE SPECIFICATION:

Please substitute the following paragraph for the paragraph at page 17, Ins. 13-19:

Please amend the paragraph at page 17, Ins. 13-19 as follows:

Since the second insulating film 115 is made of the organic insulating material, the surface can be excellently flattened. Also, since the organic resin material is generally low in permittivity, a parasitic capacitor can be reduced. However, since the organic resin material has the hygroscopic property and is not proper for a protective film, it is preferable that the second interlayer insulating

B1

✓